

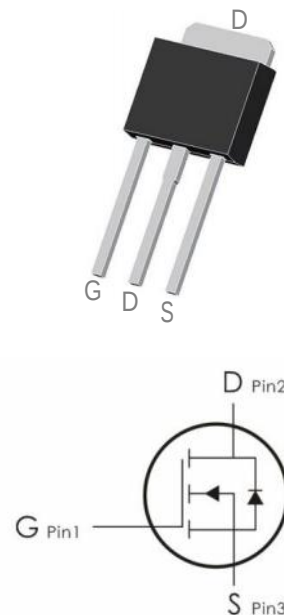
Description:

This N-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=60V, I_D=30A, R_{DS(on)} < 30m\ \Omega @ V_{GS}=10V$
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra low $R_{DS(on)}$.
- 5) Excellent package for good heat dissipation.



Absolute Maximum Ratings: ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current- $T_C=25^\circ\text{C}$	30	A
	Continuous Drain Current- $T_C=100^\circ\text{C}$	20	A
I_{DM}	Pulse Drain Current Tested <i>note1</i>	120	A
P_D	Power Dissipation- $T_C=25^\circ\text{C}$	55	W
E_{AS}	Single pulse avalanche energy <i>note2</i>	23	mJ
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +175	$^\circ\text{C}$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	2.7	$^\circ\text{C}/\text{W}$

Package Marking and Ordering Information:

Part NO.	Marking	Package
DOU30N06	30N06	TO-251

Electrical Characteristics: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Sourctce Breakdown Voltage	V _{GS} =0V, I _D =250 μ A	60	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{Ds} =60V, V _{GS} =0V	---	---	1	μ A
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ± 20V, V _{Ds} =0A	---	---	± 100	nA
On Characteristics						
V _{GS(th)}	GATE-Source Threshold Voltage	V _{GS} =V _{Ds} , I _D =250 μ A	1	1.6	2.5	V
R _{DS(ON)}	Drain-Source On Resistance ^{note3}	V _{GS} =10V, I _D =15A	---	21	30	m Ω
		V _{GS} =4.5V, I _D =10A	---	28	40	m Ω
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{Ds} =25V, V _{GS} =0V, f=1MHz	---	1450	---	pF
C _{Oss}	Output Capacitance		---	70	---	
C _{rss}	Reverse Transfer Capacitance		---	60	---	
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{Ds} =30V, I _D =15A R _G =1.8Ω, V _{GS} =10V	---	7.5	---	ns
t _r	Rise Time		---	21	---	ns
t _{d(off)}	Turn-Off Delay Time		---	16	---	ns
t _f	Fall Time		---	23.5	---	ns
Q _g	Total Gate Charge	V _{GS} =10V, V _{Ds} =30V, I _D =15A	---	25	---	nC
Q _{gs}	Gate-Source Charge		---	4.5	---	nC
Q _{gd}	Gate-Drain “Miller” Charge		---	6.5	---	nC
Drain-Source Diode Characteristics						
I _S	Continuous Source Current	---	---	---	30	A
I _{SM}	Pulsed Source Current	---	---	---	120	A

V_{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =30A	---	---	1.2	V
T_{rr}	Reverse Recovery Time	I _F =30A, dI/dt=100A/μs	---	29	---	ns
Q_{rr}	Reverse Recovery Charge		---	45	---	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. EAS condition : T_J=25°C, V_{DD}=30V, V_G=10V, L=0.5mH, R_G=25Ω, I_{AS}=9.6A
3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Typical Characteristics: (T_A=25°C unless otherwise noted)

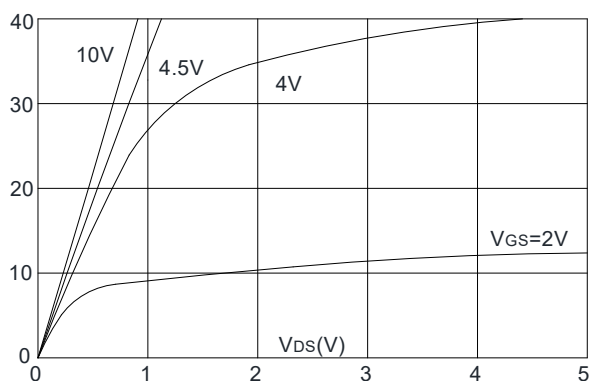


Figure1: Output Characteristics

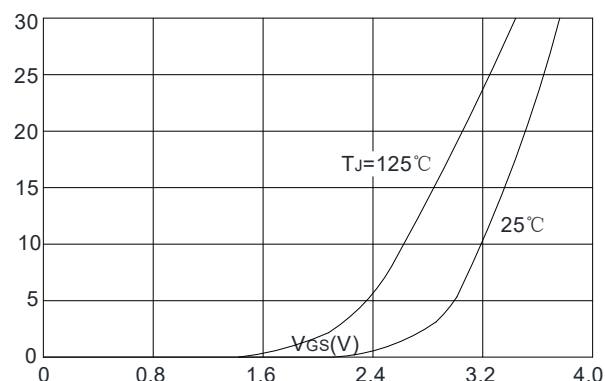


Figure 2: Typical Transfer Characteristics

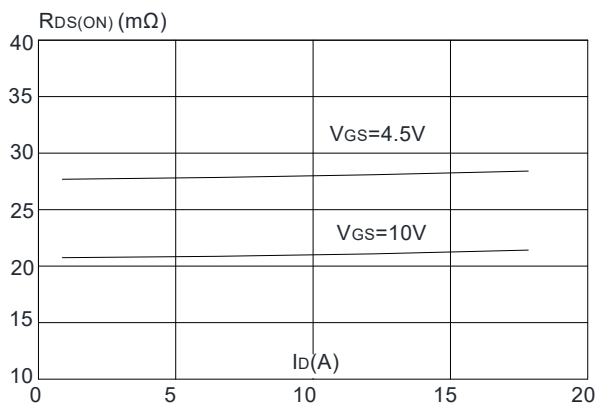


Figure 3: On-resistance vs. Drain Current

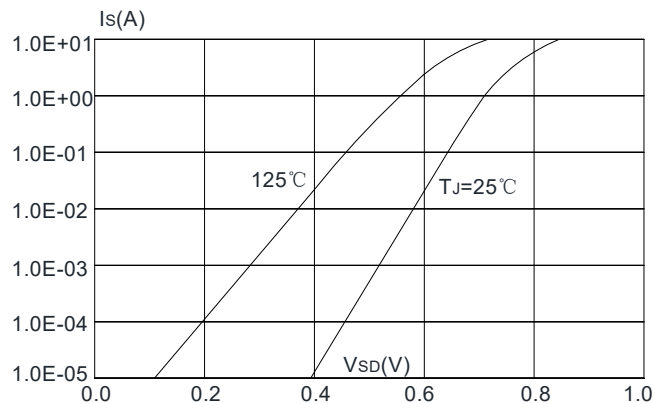


Figure 4: Body Diode Characteristics

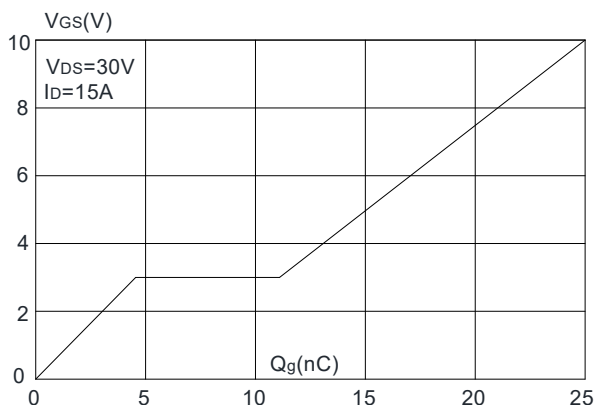


Figure 5: Gate Charge Characteristics

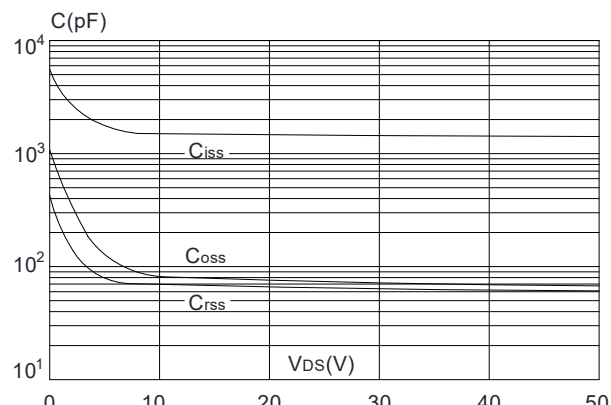


Figure 6: Capacitance Characteristics

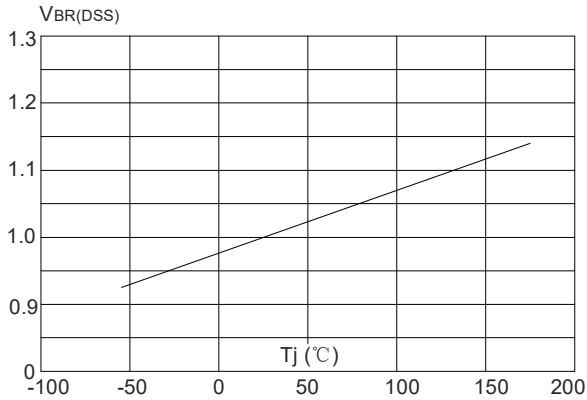


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

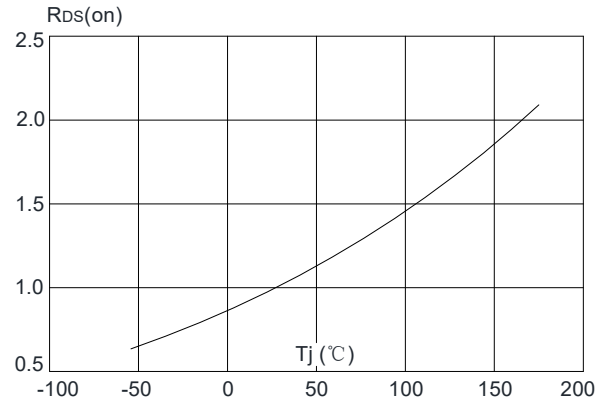


Figure 8: Normalized on Resistance vs. Junction Temperature

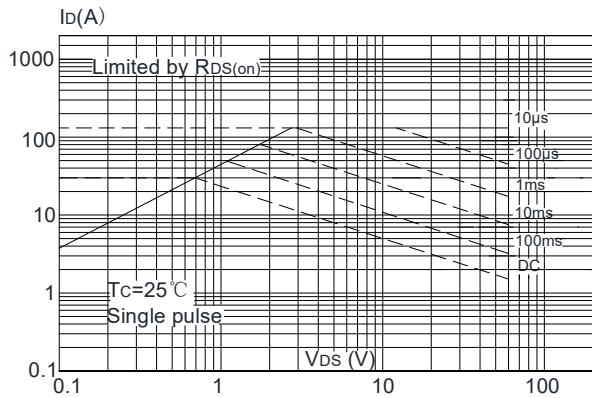


Figure 9: Maximum Safe Operating Area

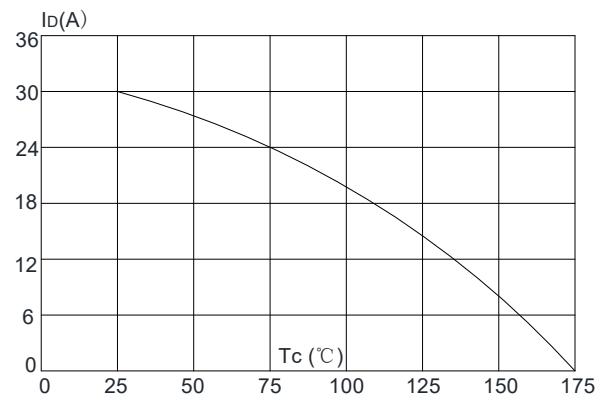


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

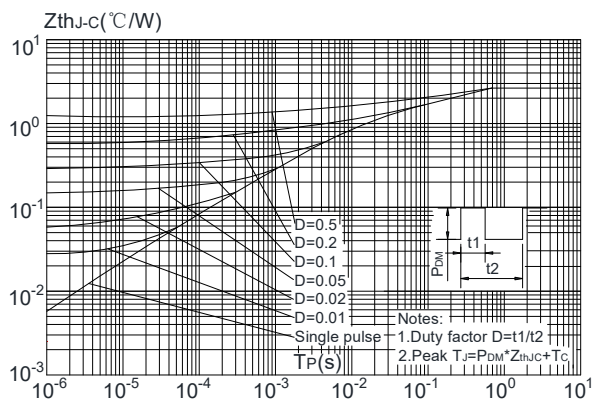


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case